

XD54563 DIP-18

DESCRIPTION

XD54563 is an eight-circuit output-sourcing Darlington transistor array. The circuits are made of PNP and NPN transistors. This semiconductor integrated circuit performs high-current driving with extremely low input-current supply.

FEATURES

- High breakdown voltage (BVcEo ≥ 50V)
- High-current driving (Io(max) = −500mA)
- With clamping diodes
- Driving available with PMOS IC output of 6 ~ 16V or with TTL output
- Wide operating temperature range (Ta = -20 to +75°C)
- Output current-sourcing type

APPLICATION

Drives of relays, printers, LEDs, fluorescent display tubes and lamps, and interfaces between MOS-bipolar logic systems and relays, solenoids, or small motors

FUNCTION

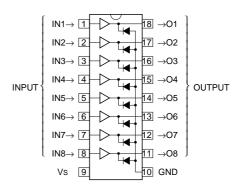
The XD54563 each have eight circuits,

which are made of input inverters and current-sourcing outputs. The outputs are made of PNP transistors and NPN Darlington transistors. The PNP transistor base current is constant. A clamping diode is provided between each output and GND. Vs and GND are used commonly among the eight circuits.

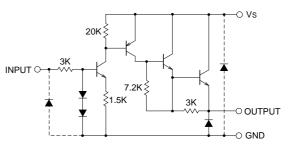
The inputs have resistance of $3k\Omega$, and voltage of up to 10V is applicable. Output current is 500 mA maximum. Supply voltage Vs is 50V maximum.

The XD54563 is enclosed in a molded small flat package, enabling space-saving design.

PIN CONFIGURATION



CIRCUIT DIAGRAM



The eight circuits share the Vs and GND.

The diode, indicated with the dotted line, is parasitic, and cannot be used.

Unit : Ω

ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted, Ta = $-20 \sim +75$ °C)

Symbol	Parameter	Conditions	Ratings	Unit
VCEO #	Collector-emitter voltage	Output, L	− 0.5 ~ + 50	V
Vs	Supply voltage		50	V
VI	Input voltage		− 0.5 ~ + 10	V
lo	Output current	Current per circuit output, H	-500	mA
lF	Clamping diode forward current		-500	mA
VR #	Clamping diode reverse voltage		50	V
Pd	Power dissipation	Ta = 25°C, when mounted on board	1.79(P)/1.10(FP)	W
Topr	Operating temperature		−20 ~ +75	°C
Tstg	Storage temperature		−55 ~ + 125	°C

^{#:} Unused I/O pins must be connected to GND.

RECOMMENDED OPERATING CONDITIONS (Unless otherwise noted, Ta = $-20 \sim +75^{\circ}$ C)

Cumphal	Parameter			4: ما ا		
Symbol			min	typ	max	Unit
Vs	Supply voltage		0	_	50	V
lo	Output current (Current per 1 cir- cuit when 8 circuits are coming on si- multaneously)	Duty Cycle P: no more than 8% FP: no more than 5%	0	_	-350	^
		Duty Cycle P: no more than 55% FP: no more than 30%	0	_	-100	mA
VIH	"H" input voltage	·	2.4	_	10	V
VIL	"L" input voltage		0	_	0.2	V

ELECTRICAL CHARACTERISTICS (Unless otherwise noted, $Ta = -20 \sim +75$ °C)

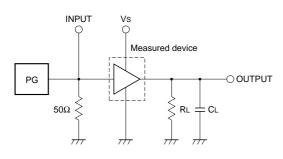
Symbol	Parameter	Test conditions	Limits			l lmit
			min	typ*	max	Unit
IS (leak) #	Supply leak current	Vs = 50V, VI = 0.2V	_	_	100	μΑ
VCE (sat)	Collector-emitter saturation voltage	Vs = 10V, VI = 2.4V, Io = -350mA		1.6	2.4	V
		Vs = 10V, VI = 2.4V, Io = -100mA	_	1.45	2.0	
lı	Input current	VI = 3V	_	0.6	1.0	mA
		VI = 10V	_	2.9	5.0	
Is	Supply current	Vs = 50V, VI = 3V (all input)	_	5.6	15.0	mA
VF	Clamping diode forward voltage	IF = -350mA	_	-1.2	-2.4	V
IR #	Clamping diode reverse current	VR = 50V	_	_	100	μΑ

^{*:} The typical values are those measured under ambient temperature (Ta) of 25°C. There is no guarantee that these values are obtained under any conditions.
#: Unused I/O pins must be connected to GND.

SWITCHING CHARACTERISTICS (Unless otherwise noted, Ta = 25°C)

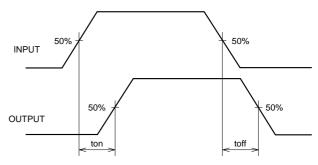
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	Unit
ton	Turn-on time	CL = 15pF (note 1)	_	100	_	ns
toff	Turn-off time		_	4800	_	ns

NOTE 1 TEST CIRCUIT



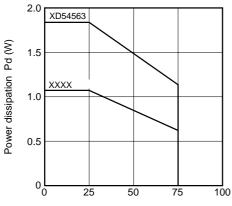
- (1) Pulse generator (PG) characteristics : PRR = 1kHz, tw = 10 μ s, tr = 6ns, tf = 6ns, Zo = 50 Ω Vı = 0 to 2.4V
- (2) Input-output conditions : $RL = 30\Omega$, Vs = 10V
- (3) Electrostatic capacity CL includes floating capacitance at connections and input capacitance at probes

TIMING DIAGRAM

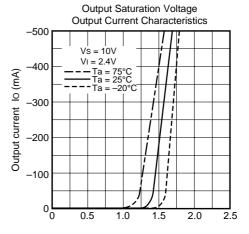


TYPICAL CHARACTERISTICS

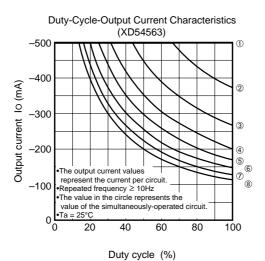
Thermal Derating Factor Characteristics



Ambient temperature Ta (°C)



Output saturation voltage VCE (sat) (V)

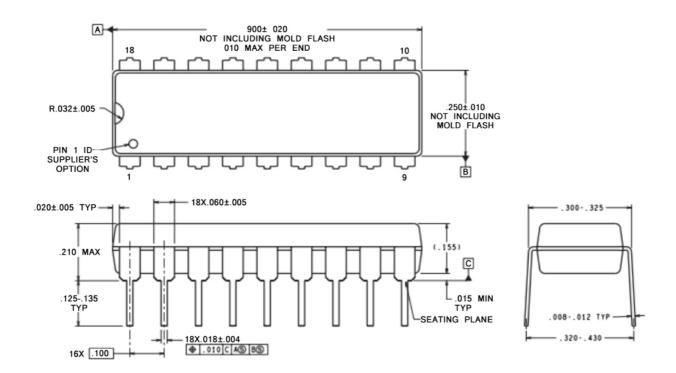


Duty-Cycle-Output Current Characteristics (XD54563) -500 400 Output current Io (mA) -300 -200 The output current values
represent the current per circuit.

Repeated frequency ≥ 10Hz

The value in the circle represents the (4) (5) (6) (7) (8) -100 value of the simultaneously-operated 40 60 100 20 80 Duty cycle (%)

DIP



以上信息仅供参考. 如需帮助联系客服人员。谢谢 XINLUDA

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